Optimization of Heteroepitaxial $ZnGeN_2$/GaN Quantum Wells for Green LEDs

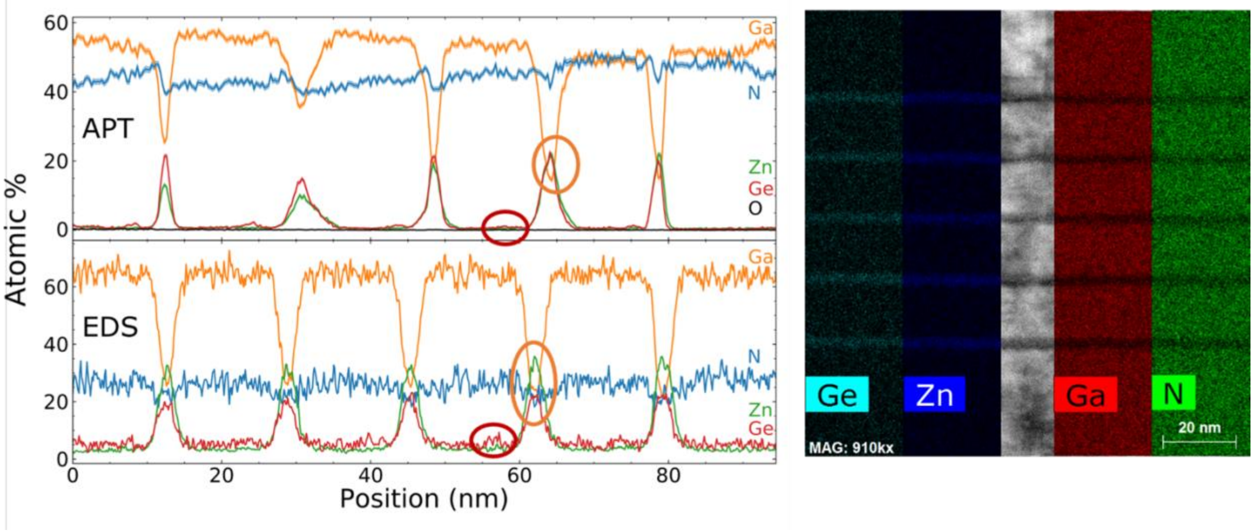

Figure 1: (left) APT (top) and EDS (bottom) of the $ZnGeN_2$/GaN five-unit quantum well, showing unintentional incorporation of Ge and Ga; (right) STEM/EDS of a 5 MQW $ZnGeN_2$/ GaN heterostructure showing clear abrupt interfaces.

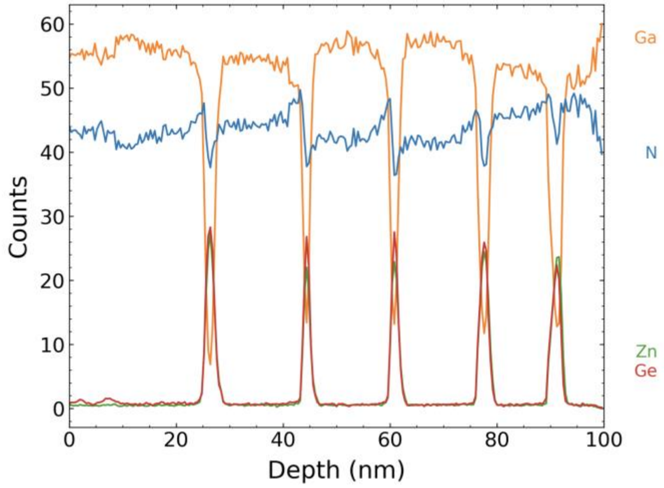

Figure 2: APT of the optimized $ZnGeN_2$/GaN five-unit quantum well, showing reduced unintentional incorporation of Ge and Ga.